

WHAT IS CLAIMED IS

1. An interconnecting structure comprising:
first wirings formed on a substrate;
5 a low-k dielectric film formed on the first wirings, the low-k dielectric film having dielectric constant of 3 or less;
vias formed in the low-k dielectric film and connected to the first wiring;
second wirings formed on the vias and connected to the vias;
10 and
dummy vias formed on the periphery of an isolated via of the vias.
2. The interconnecting structure according to claim 1, further comprising a cap film formed on the low-k dielectric film,
15 wherein the second wiring is formed in the cap film and the low-k dielectric film.
3. The interconnecting structure according to claim 1, further comprising:
20 first dummy wirings formed on the periphery of the first wirings;
and
second dummy wirings formed on the periphery of the second wirings,
25 wherein the dummy vias are connected to the first and second dummy wirings, and the first or second dummy wirings connected to the dummy vias are connected to a ground potential.
4. The interconnecting structure according to claim 1, wherein
30 the dummy vias have a slit shape.

5. The interconnecting structure according to claim 1, wherein the dimension of the dummy vias is 1 to 10 times the minimum dimension of the vias.